# **FUJITSU**

# MB834000A/AL

## CMOS 4M-BIT MASK READ ONLY MEMORY

#### 512K x 8 CMOS MASK READ ONLY MEMORY

The Fujitsu MB834000A/AL is a CMOS Si-gate mask-programmable static read only memory organized as 524, 288 words by 8 bits.

All pins are TTL-compatible and 3-state output level. The device is fully-static operatable (i.e. no need of clock signal) with a single +5V power supply. Also, the MB834000AL can be used with a single +3V power supply which is required for battery powered applications.

The MB834000A/AL is designed for applications such as character generator and program strage which require large memory capacity and high–speed/low–power operation.

- Organization: 524, 288 words x 8 bits
- Access time: 200ns max. @ Vcc = 5V (MB834000A) 400ns max. @ Vcc = 3V (MB834000AL)
- Completely static operation: No clock required
- TTL compatible Input/Output
- Three state output
- Single +5V power supply (MB834000A/AL) Single +3V power supply (MB834000AL)
- Power dissipation: 220mW max. (Active) @ Vcc = 5V (MB834000A/AL)
   40mW max. (Active) @ Vcc = 3V (MB834000AL)
- JEDEC standard 32-pin Plastic DIP: Suffix: P
- 32-pin Plastic Small Outline Package (SOP): Suffix: PF
- 32-pin Plastic Thin Small Outline Package (TSOP):

Suffix: PFTN(Normal Bend)
Suffix: PFTR(Reversed Bend)

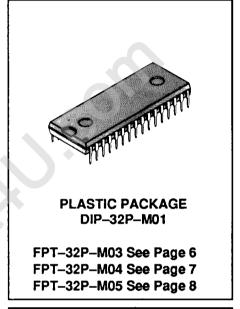
#### ABSOLUTE MAXIMUM RATINGS (see NOTE)

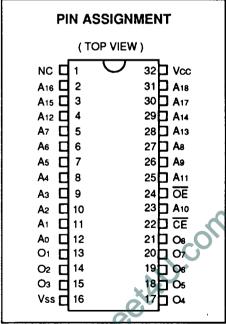
Rating	Symbol	Value	Unit	
Supply Voltage	Vcc	-0.3 to +7.0 *	٧	
Input Voltage	Vin	-0.5 to Vcc +0.5 *	٧	
Output Voltage	Vout	-0.5 to Vcc +0.5 *	٧	
Temperature Under Bias	TBIAS	-10 to +85	°C	
Storage Temperature Range	Тѕтс	-45 to +125	°c	

#### \* Referenced to GND

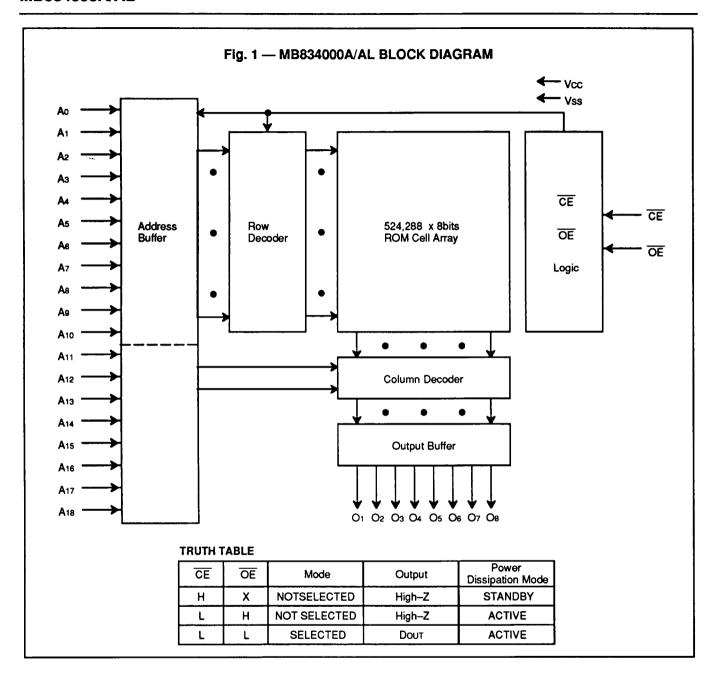
NOTE

Permanent device damage may occur if the above Absolute Maximum Ratings are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.



# CAPACITANCE (TA=25° C, f=1MHz)

Parameter	Symbol	Min	Тур	Max	Unit
Output Capacitance (Vouт=0V)	Соит			15	pF
Input Capacitance (VIN=0V)	Cin			10	pF

## RECOMMENDED OPERATING CONDITIONS

(Referenced to GND)

Parameter	Symbol	MB834000A/AL			MB834000AL			Unit	
	Symbol	Min	Тур	Max	Min	Тур	Max	J	
Supply Voltage	Vcc	4.5	5.0	5.5	2.7	3.0	3.3	V	
Ambient Temperature	TA	0		70	0		70	°c	

## DC CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

Parameter	Test Condition	Symbol	MB834000A/AL			MB834000AL			Unit
			Min	Тур	Max	Min	Тур	Max	J
Active Supply Current	CE=VIL, Minimum Cycle Output = Open	lcc			50			12	mA
Standby Synaly Cymnat	CE=VIH	ISB1			1			0.5	mA
Standby Supply Current	CE=Vcc=ViH, Vin=GND or Vcc	ISB2			10			10	μА
Input Leakage Current	Vin=0 to Vcc	lu	-10		10	<b></b> 5		5	μА
Output Leakage Current	CE=VIH OE=VIH	ILVO	-10		10	<b>-</b> 5		5	μA
Input Low Voltage		VIL	0.3		0.8	-0.3		0.6	٧
Input High Voltage		Viн	2.2		Vcc+0.3	Vccx0.7		Vcc+0.3	٧
Output High Voltage	Іон=–400μА	Voн	2.4			2.0			٧
Output Low Voltage	IOL=2.1mA IOL=1.0mA	Vol			0.4			0.4	٧

### Fig. 2 — AC TEST CONDITIONS

Input Pulse Level

: 0.6 to 2.4V @Vcc = 5V (MB834000A/AL) 0.4 to Vccx0.8V @Vcc = 3V(MB834000AL)

• Input Pulse Rise and Fall Time : t⊤=5ns

• Timing Reference Levels

: tr=ons

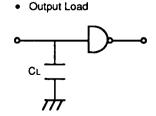
: Input: ViL=0.8V, ViH=2.2V / Output: VoL=0.8V, VoH=2.2V

@Vcc = 5V (MB834000A/AL)

: Input:  $V_{IL}=0.6V$ ,  $V_{IH}=V_{CCX}0.7V$  / Output:  $V_{OL}=V_{OH}=1.5V$ 

@Vcc = 3V (MB834000AL)

: 1 TTL Gate and 100pF

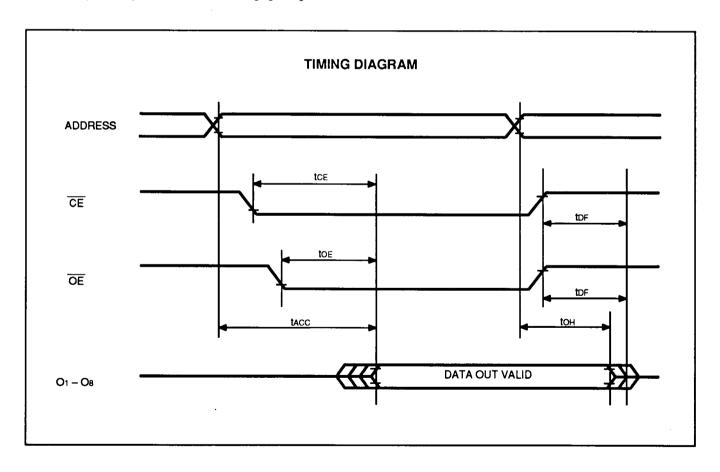


# **AC CHARACTERISTICS**

(Recommended operating conditions unless otherwise noted.)

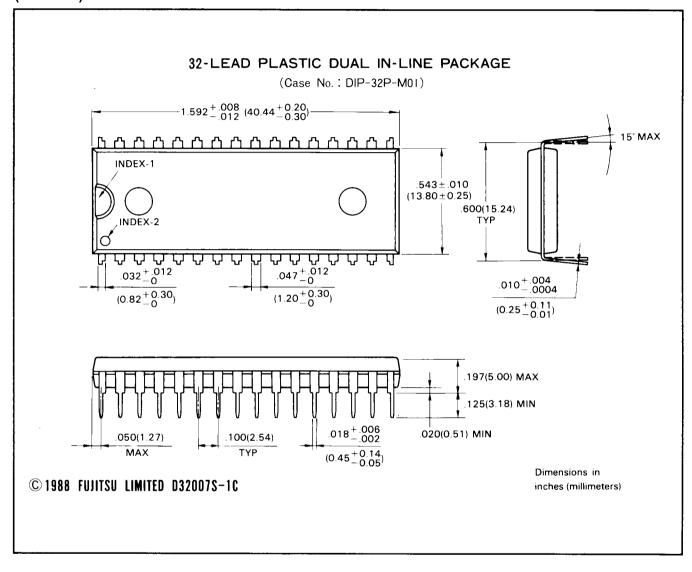
Parameter	Test Condition	Symbol	MB834	000 <b>A</b> /AL	MB83		
			Min	Max	Min	Max	Unit
Address Access Time	CE=OE=VIL	tacc		200		400	ns
Chip Enable Access Time	OE=VIL	tcE		200		400	ns
Output Enable Access Time		toE		80		200	ns
Output Disable Time*2		tDF	-	60		120	ns
Output Hold Time	CE=OE=VIL	tон	0		0		ns

<sup>\*1:</sup> When contineously switching between 3V operation and 5V operation, during VCC transition the CE should be High state (Standby mode).
\*2: tDF is specified by either of CE or OE changing to High earlier.



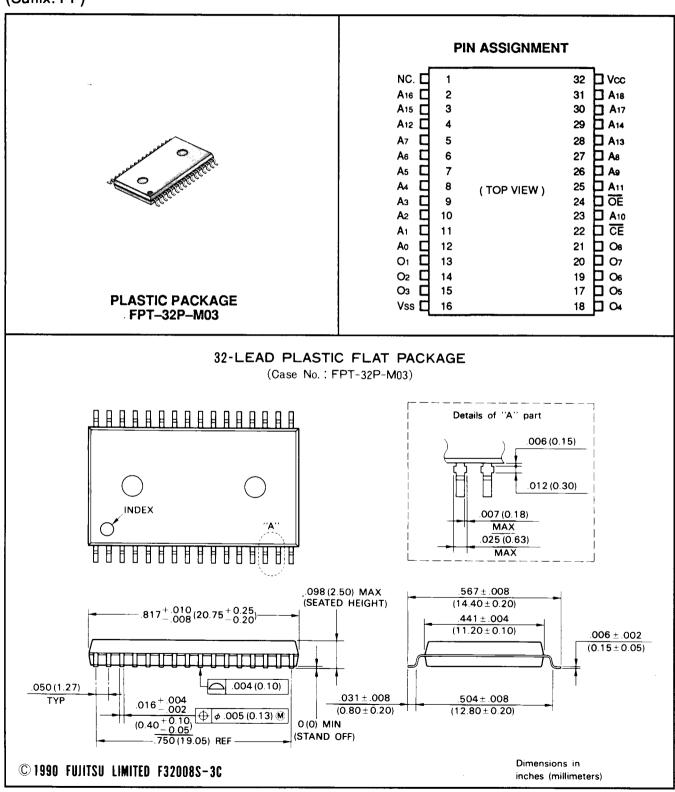
## **PACKAGE DIMENSIONS**

(Suffix: P)



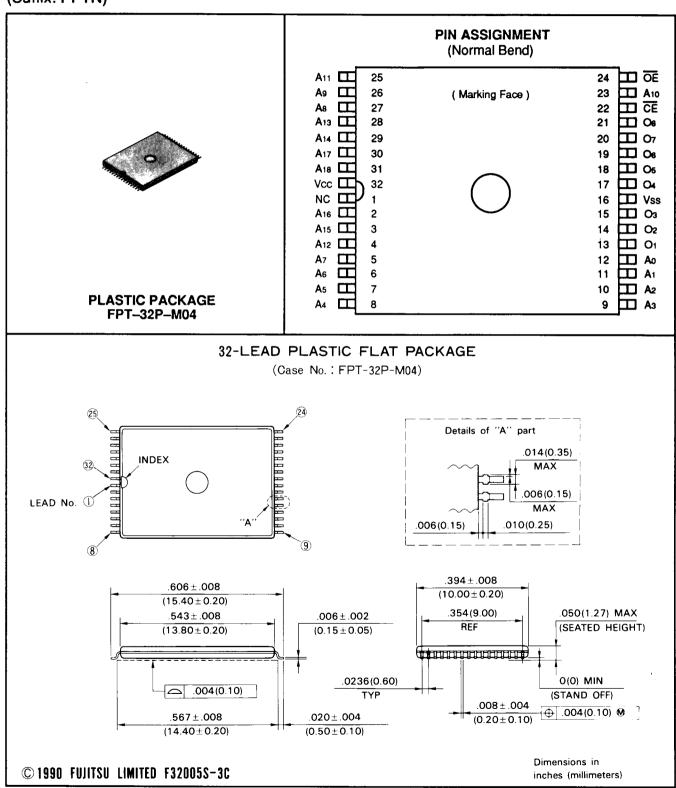
# PACKAGE DIMENSIONS (Continued)

(Suffix: PF)



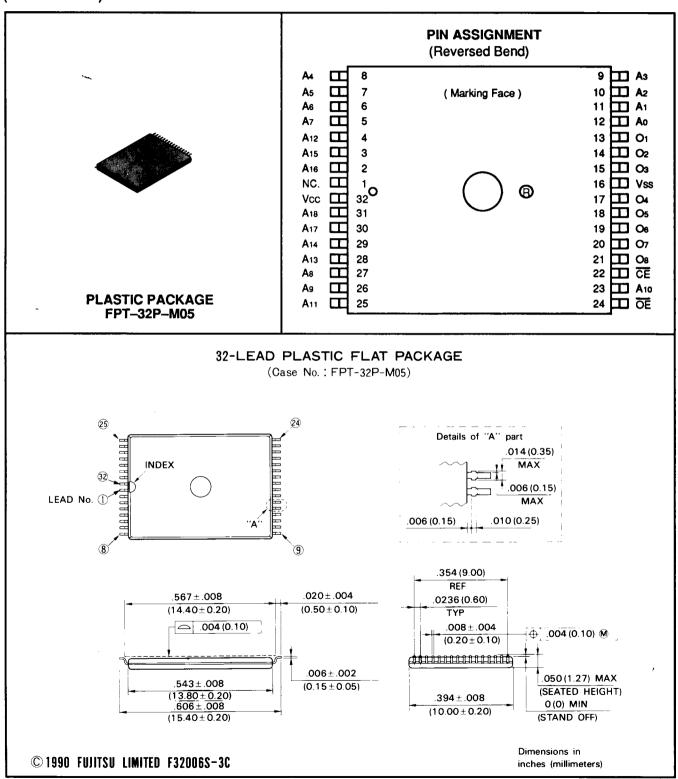
# PACKAGE DIMENSIONS (Continued)

(Suffix: PFTN)



# PACKAGE DIMENSIONS (Continued)

(Suffix: PFTR)



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